

of pixels on the thin film transistor panel and masks the portion of the thin film transistor panel that is most likely to incur light-leakage problems. The black matrix can also be a photo mask in the step of etching the transparent insulator for exposing the transparent electrode. In this case, a back exposure process is used (expose from the transparent substrate side of the thin film transistor panel). A positive photoresist on the bottom of the transparent insulator will be exposed without an additional photo mask. A subsequent photolithographic process can be performed to generate a suitable contact via on the transparent insulator. The contact via allows the transparent electrode to be exposed from the transparent insulator side of the thin film transistor panel. Hence, this traditionally complicated process is simplified, and productivity is increased.

IN THE CLAIMS:

Please **cancel claim 11** without prejudice to or disclaimer of the subject matter contained therein.

Please **amend claims 1-10 and 12-37** as follows:

1. (Amended) A method for manufacturing a thin film transistor panel, comprising at least the following steps: